

Title (en)
NANOFIN TUNNELING TRANSISTORS

Title (de)
NANOFIN-TUNNELTRANSISTOR

Title (fr)
TRANSISTORS À NANO-AILETTES À EFFET TUNNEL

Publication
EP 2002469 A1 20081217 (EN)

Application
EP 07754622 A 20070403

Priority

- US 2007008124 W 20070403
- US 39752706 A 20060404
- US 39743006 A 20060404
- US 39735806 A 20060404
- US 39741306 A 20060404
- US 39740606 A 20060404

Abstract (en)
[origin: WO2007114927A1] One aspect of the present subject matter relates to a method for forming a transistor. According to an embodiment, a fin is formed from a crystalline substrate. A first source/drain region is formed in the substrate beneath the fin. A surrounding gate insulator is formed around the fin. A surrounding gate is formed around the fin and separated from the fin by the surrounding gate insulator. A second source/drain region is formed in a top portion of the fin. Various embodiments etch a hole in a layer over the substrate, form sidewall spacers in the hole, form a fin pattern from the sidewall spacers, and etch into the crystalline substrate to form the fin from the substrate using a mask corresponding to the fin pattern. Other aspects are provided herein.

IPC 8 full level
H01L 21/336 (2006.01); **H01L 21/20** (2006.01); **H01L 21/8242** (2006.01); **H01L 29/06** (2006.01); **H01L 29/786** (2006.01)

CPC (source: EP KR)
B82Y 10/00 (2013.01 - EP); **H01L 27/105** (2013.01 - EP KR); **H01L 29/0665** (2013.01 - EP KR); **H01L 29/0673** (2013.01 - EP KR); **H01L 29/42392** (2013.01 - EP KR); **H01L 29/66666** (2013.01 - EP KR); **H01L 29/66742** (2013.01 - EP KR); **H01L 29/66825** (2013.01 - KR); **H01L 29/7827** (2013.01 - EP KR); **H01L 29/78642** (2013.01 - EP KR); **H10B 12/053** (2023.02 - KR); **H10B 99/00** (2023.02 - EP KR); **H01L 29/66825** (2013.01 - EP); **H10B 12/053** (2023.02 - EP)

Citation (search report)
See references of WO 2007120493A1

Designated contracting state (EPC)
AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HU IE IS IT LI LT LU LV MC MT NL PL PT RO SE SI SK TR

DOCDB simple family (publication)
WO 2007114927 A1 20071011; EP 2002468 A1 20081217; EP 2002468 B1 20130724; EP 2002469 A1 20081217; EP 2002470 A2 20081217; EP 2002470 B1 20160309; EP 2008309 A1 20081231; JP 2009532903 A 20090910; JP 2009532904 A 20090910; JP 2009532905 A 20090910; JP 2009532907 A 20090910; JP 5229587 B2 20130703; JP 5229635 B2 20130703; JP 5234439 B2 20130710; KR 101378256 B1 20140325; KR 101474028 B1 20141217; KR 20090005149 A 20090112; KR 20090006169 A 20090114; KR 20090007393 A 20090116; KR 20090007397 A 20090116; KR 20140051463 A 20140430; SG 170827 A1 20110530; SG 172643 A1 20110728; WO 2007120492 A1 20071025; WO 2007120493 A1 20071025; WO 2007136461 A2 20071129; WO 2007136461 A3 20080117

DOCDB simple family (application)
US 2007008400 W 20070403; EP 07754621 A 20070403; EP 07754622 A 20070403; EP 07754850 A 20070403; EP 07809002 A 20070403; JP 2009504232 A 20070403; JP 2009504238 A 20070403; JP 2009504239 A 20070403; JP 2009504280 A 20070403; KR 20087026970 A 20081103; KR 20087026973 A 20081103; KR 20087027075 A 20081104; KR 20087027077 A 20081104; KR 20147009477 A 20070403; SG 2011023819 A 20070403; SG 2011038726 A 20070403; US 2007008084 W 20070403; US 2007008123 W 20070403; US 2007008124 W 20070403